

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2022

DESCRIPTION

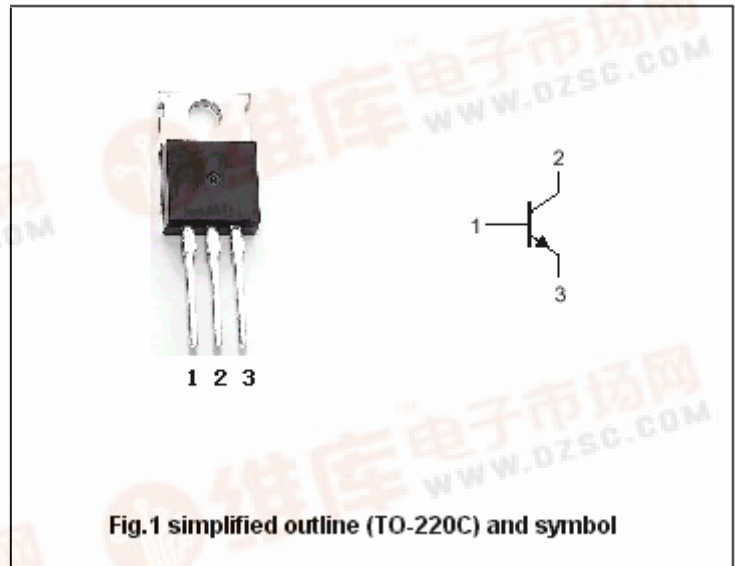
- With TO-220C package
- High voltage

APPLICATIONS

- Series regulator, switch, and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		1	A
P _C	Collector dissipation	T _C =25℃	30	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-50~150	℃

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CHARACTERISTICS

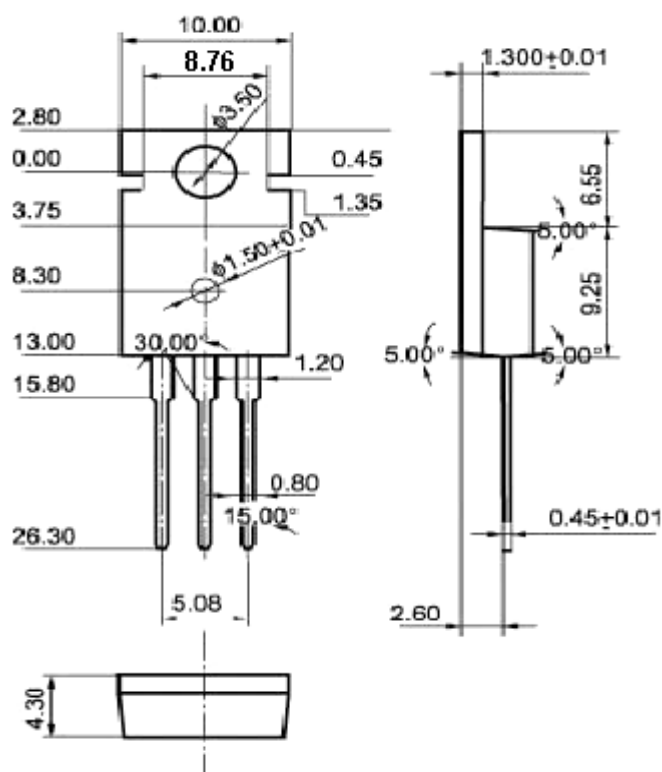
 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25\text{mA}$; $I_B=0$	300			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1\text{mA}$; $I_E=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=500\text{mA}$; $I_B=100\text{mA}$			1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=300\text{V}$; $I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6\text{V}$; $I_C=0$			1.0	mA
h_{FE}	DC current gain	$I_C=200\text{mA}$; $V_{CE}=4\text{V}$	30			
f_T	Transition frequency	$I_C=100\text{mA}$; $V_{CE}=12\text{V}$		10		MHz

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)